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October 2011

FOD3150 High Noise Immunity, 1.0A Output Current, Gate Drive Optocoupler

Features

- High noise immunity characterized by 20kV/µs minimum common mode rejection
- Use of P-channel MOSFETs at output stage enables output voltage swing close to the supply rail
- Wide supply voltage range from 15V to 30V
- Fast switching speed
 - 500ns max. propagation delay
 - 300ns max. pulse width distortion
- Under Voltage LockOut (UVLO) with hysteresis
- Extended industrial temperate range, -40°C to 100°C temperature range
- Safety and regulatory approvals
 - UL1577, 5000 V_{RMS} for 1 min.
 - IEC60747-5-2
- >8.0mm clearance and creepage distance (option 'T')

Applications

- Industrial inverter
- Uninterruptible power supply
- Induction heating
- Isolated IGBT/Power MOSFET gate drive

Description

The FOD3150 is a 1.0A Output Current Gate Drive Optocoupler, capable of driving most 800V/20A IGBT/MOSFET. It is ideally suited for fast switching driving of power IGBT and MOSFETs used in motor control inverter applications, and high performance power system.

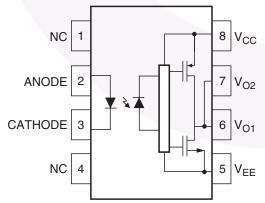
It utilizes Fairchild's patented coplanar packaging technology, Optoplanar®, and optimized IC design to achieve high noise immunity, characterized by high common mode rejection.

It consists of a gallium aluminum arsenide (AlGaAs) light emitting diode optically coupled to an integrated circuit with a high-speed driver for push-pull MOSFET output stage.

Related Resources

- FOD3120, 2.5A Output Current, Gate Drive Optocoupler Datasheet
- www.fairchildsemi.com/products/opto/

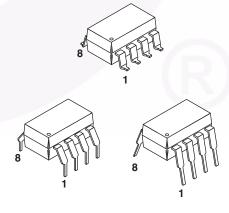
Functional Block Diagram



Note:

A 0.1µF bypass capacitor must be connected between pins 5 and 8.

Package Outlines



Truth Table

LED	V _{CC} -V _{EE} "Positive Going" (Turn-on)	V _{CC} –V _{EE} "Negative Going" (Turn-off)	v _o
Off	0V to 30V	0V to 30V	Low
On	0V to 11V	0V to 9.5V	Low
On	11V to 13.5V	9.5V to 12V	Transition
On	13.5V to 30V	12V to 30V	High

Pin Definitions

Pin #	Name	Description
1	NC	Not Connected
2	Anode	LED Anode
3	Cathode	LED Cathode
4	NC	Not Connected
5	V _{EE}	Negative Supply Voltage
6	V _{O2}	Output Voltage 2 (internally connected to V _{O1})
7	V _{O1}	Output Voltage 1
8	V _{CC}	Positive Supply Voltage

Safety and Insulation Ratings

As per IEC 60747-5-2. This optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Symbol	Parameter	Min.	Тур.	Max.	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1				
	For Rated Main Voltage < 150Vrms		I–IV		
	For Rated Main Voltage < 300Vrms		I–IV		
	For Rated Main Voltage < 450Vrms		I–III		
	For Rated Main Voltage < 600Vrms		I–III		
	Climatic Classification		55/100/21		
	Pollution Degree (DIN VDE 0110/1.89)		2		
CTI	Comparative Tracking Index	175			
V _{PR}	Input to Output Test Voltage, Method b, V _{IORM} x 1.875 = V _{PR} , 100% Production Test with tm = 1 sec., Partial Discharge < 5pC	1669			
	Input to Output Test Voltage, Method a, V _{IORM} x 1.5 = V _{PR} , Type and Sample Test with tm = 60 sec.,Partial Discharge < 5 pC	1335			
V _{IORM}	Max Working Insulation Voltage	890			V _{peak}
V _{IOTM}	Highest Allowable Over Voltage	6000			V _{peak}
	External Creepage	8			mm
	External Clearance	7.4			mm
	External Clearance (for Option T-0.4" Lead Spacing)	10.16			mm
	Insulation Thickness	0.5			mm
	Safety Limit Values – Maximum Values Allowed in the Event of a Failure				
T _{Case}	Case Temperature	150			°C
I _{S,INPUT}	Input Current	25			mA
P _{S,OUTPUT}	Output Power (Duty Factor ≤ 2.7%)	250			mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500V	10 ⁹			Ω

Absolute Maximum Ratings (T_A = 25°C unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Value	Units
T _{STG}	Storage Temperature	-55 to +125	°C
T _{OPR}	Operating Temperature	-40 to +100	°C
T _J	Junction Temperature	-40 to +125	°C
T _{SOL}	Lead Wave Solder Temperature (refer to page 19 for reflow solder profile)	260 for 10sec	°C
I _{F(AVG)}	Average Input Current	25	mA
V _R	Reverse Input Voltage	5	V
I _{O(PEAK)}	Peak Output Current ⁽¹⁾	1.5	А
V _{CC} – V _{EE}	Supply Voltage	0 to 35	V
V _{O(PEAK)}	Peak Output Voltage	0 to V _{CC}	V
t _{R(IN)} , t _{F(IN)}	Input Signal Rise and Fall Time	500	ns
PDI	Input Power Dissipation ⁽²⁾⁽⁴⁾	45	mW
PD _O	Output Power Dissipation ⁽³⁾⁽⁴⁾	250	mW

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Value	Units
T _A	Ambient Operating Temperature	-40 to +100	°C
V _{CC} – V _{EE}	Power Supply	15 to 30	V
I _{F(ON)}	Input Current (ON)	7 to 16	mA
V _{F(OFF)}	Input Voltage (OFF)	0 to 0.8	V

Isolation Characteristics

Apply over all recommended conditions, typical value is measured at T_A = 25°C

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _{ISO}	Input-Output Isolation Voltage	$T_A = 25$ °C, R.H.< 50%, t = 1.0min, $I_{I-O} \le 10\mu A$, 50Hz ⁽⁵⁾⁽⁶⁾	5000			V _{RMS}
R _{ISO}	Isolation Resistance	$V_{I-O} = 500V^{(5)}$		10 ¹¹		Ω
C _{ISO}	Isolation Capacitance	V _{I-O} = 0V, Freq = 1.0MHz ⁽⁵⁾		1		pF

Electrical Characteristics

Apply over all recommended conditions, typical value is measured at V_{CC} = 30V, V_{EE} = Ground, T_A = 25°C unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _F	Input Forward Voltage	I _F = 10mA	1.2	1.5	1.8	V
$\Delta(V_F/T_A)$	Temperature Coefficient of Forward Voltage			-1.8		mV/°C
BV _R	Input Reverse Breakdown Voltage	I _R = 10μA	5			V
C _{IN}	Input Capacitance	f = 1MHz, VF = 0V		60		pF
I _{OH}	High Level Output Current ⁽¹⁾	$V_{O} = V_{CC} - 0.75V$	0.2			Α
		$V_O = V_{CC} - 4V$	1.0			
I _{OL}	Low Level Output Current ⁽¹⁾	$V_{O} = V_{CC} + 0.75V$	0.2			Α
		$V_O = V_{CC} + 4V$	1.0			
V _{OH}	High Level Output Voltage	I _F = 10mA, I _O = -1A	V _{CC} – 4V	V _{CC} – 6V		V
		$I_F = 10mA, I_O = -100mA$	V _{CC} - 0.5V	V _{CC} - 0.1V		
V _{OL}	Low Level Output Voltage	$I_F = 0mA$, $I_O = 1A$		V _{EE} + 6V	V _{EE} + 4V	V
		$I_F = 0mA, I_O = 100mA$		V _{EE} + 0.1V	V _{EE} + 0.5V	
I _{CCH}	High Level Supply Current	V _O = Open, I _F = 7 to 16mA		2.8	5	mA
I _{CCL}	Low Level Supply Current	V_O = Open, V_F = 0 to 0.8V		2.8	5	mA
I _{FLH}	Threshold Input Current Low to High	$I_{O} = 0 \text{mA}, V_{O} > 5 \text{V}$		2.3	5.0	mA
V_{FHL}	Threshold Input Voltage High to Low	I _O = 0mA, V _O < 5V	0.8			V
V _{UVLO+}	Under Voltage Lockout	I _F = 10mA, V _O > 5V	11	12.7	13.5	V
V _{UVLO} _	Threshold	I _F = 10mA, V _O < 5V	9.5	11.2	12.0	V
UVLO _{HYS}	Under Voltage Lockout Threshold Hysteresis			1.5		V

Switching Characteristics

Apply over all recommended conditions, typical value is measured at $V_{CC} = 30V$, $V_{EE} = Ground$, $T_A = 25^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
t _{PHL}	Propagation Delay Time to Logic Low Output	I_F = 7mA to 16mA, Rg = 20 Ω , Cg =10nF,	100	275	500	ns
t _{PLH}	Propagation Delay Time to Logic High Output	f = 10kHz, Duty Cycle = 50%	100	255	500	ns
PWD	Pulse Width Distortion,			20	300	ns
PDD (Skew)	Propagation Delay Difference Between Any Two Parts or Channels, (t _{PHL} - t _{PLH}) ⁽⁷⁾		-350		350	ns
t _r	Output Rise Time (10% – 90%)			60		ns
t _f	Output Fall Time (90% – 10%)			60		ns
t _{UVLO ON}	UVLO Turn On Delay	I _F = 10mA , V _O > 5V		1.6		μs
t _{UVLO} OFF	UVLO Turn Off Delay	I _F = 10mA , V _O < 5V		0.4		μs
I CM _H I	Common Mode Transient Immunity at Output High	$T_A = 25$ °C, $V_{CC} = 30$ V, $I_F = 7$ to 16mA, $V_{CM} = 2000$ V ⁽⁸⁾	20	50		kV/μs
I CM _L I	Common Mode Transient Immunity at Output Low	$T_A = 25$ °C, $V_{CG} = 30$ V, $V_F = 0$ V, $V_{CM} = 2000$ V	20	50		kV/μs

Notes:

- 1. Maximum pulse width = 10µs, maximum duty cycle = 0.2%
- 2. Derate linearly above 87°C, free air temperature at a rate of 0.77mW/°C
- 3. No derating required across temperature range.
- 4. Functional operation under these conditions is not implied. Permanent damage may occur if the device is subjected to conditions outside these ratings.
- 5. Device is considered a two terminal device: Pins 2 and 3 are shorted together and Pins 5, 6, 7 and 8 are shorted together.
- 6. 5,000 V_{RMS} for 1 minute duration is equivalent to 6,000 VAC_{RMS} for 1 second duration.
- 7. The difference between t_{PHI} and t_{PLH} between any two FOD3150 parts under same test conditions.
- 8. Common mode transient immunity at output high is the maximum tolerable negative dVcm/dt on the trailing edge of the common mode impulse signal, Vcm, to assure that the output will remain high (i.e. $V_O > 15.0V$).
- Common mode transient immunity at output low is the maximum tolerable positive dVcm/dt on the leading edge of the common pulse signal, Vcm, to assure that the output will remain low (i.e. V_O < 1.0V).

Typical Performance Curves

Fig. 1 Output High Voltage Drop vs. Output High Current

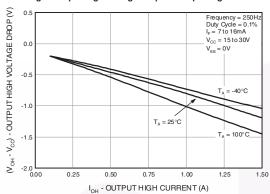


Fig. 2 Output High Voltage Drop vs. Ambient Temperature

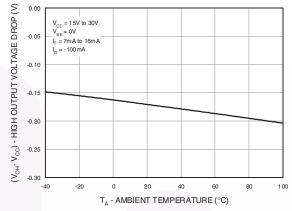


Fig. 3 Output Low Voltage vs. Output Low Current

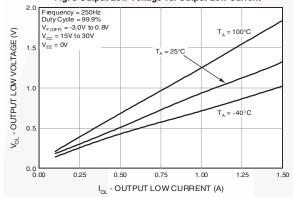


Fig. 4 Output Low Voltage vs. Ambient Temperature

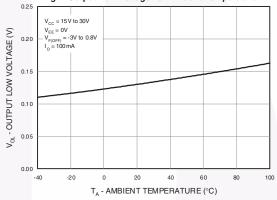


Fig. 5 Supply Current vs. Ambient Temperature

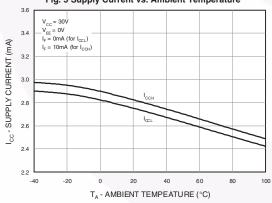
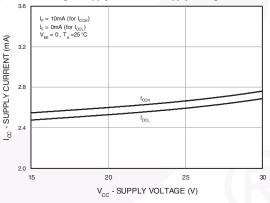
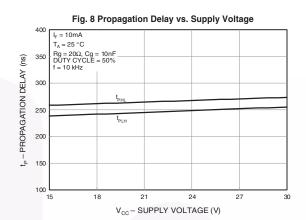


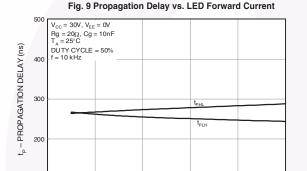
Fig. 6 Supply Current vs. Supply Voltage



Typical Performance Curves (Continued)

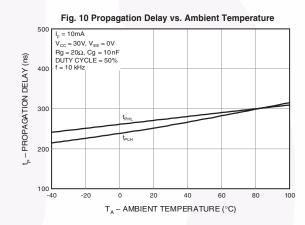
Fig. 7 Low to High Input Current Threshold vs. **Ambient Temperature** $_{\rm I_{ELH}}$ - LOW TO HIGH CURRENT THRESHOLD ($_{\rm I\!P}A$ 4.0 V_{CC} = 15 V to 30V V_{EE} = 0V Output = Open 3.5 3.0 2.5 2.0 1.5 1.0 -40 40 100 T_A - AMBIENT TEMPERATURE (°C)

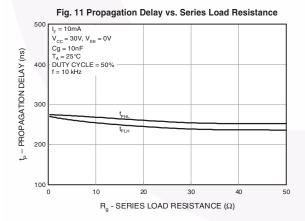


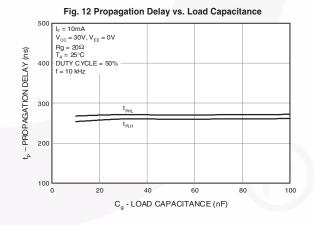


12

I_F - FORWARD LED CURRENT (mA)

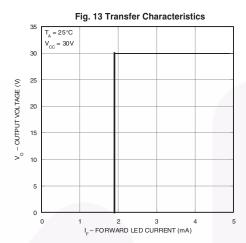


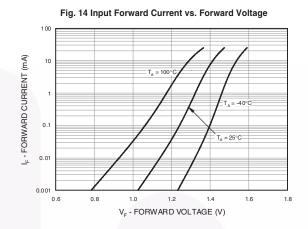


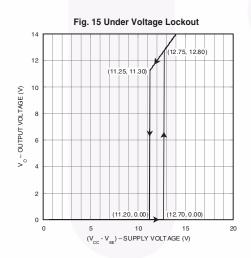


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Typical Performance Curves (Continued)







Test Circuit Power Supply $V_{CC} = 15V \text{ to } 30V$ ⊥C1 ⊤0.1μF **Pulse Generator** 8 PW = 4.99msPeriod = 5ms Pulse-In $\mathsf{R}_\mathsf{OUT} = 50\Omega$ 2 lol $\stackrel{>}{>}$ R2 100Ω Power Supply 3 V = 4V D1 V_{OL} LED-IFmon 5 4 R1 100Ω To Scope **Test Conditions:** Frequency = 200Hz Duty Cycle = 99.8% V_{CC} = 15V to 30V V_{EE} = 0V $V_{F(OFF)} = -3.0V \text{ to } 0.8V$ Figure 20. I_{OL} Test Circuit Power Supply V_{CC} = 15V to 30V - C1 - 0.1μF **Pulse Generator** 8 PW = 10μs Period = 5ms Pulse-In $R_{OUT} = 50\Omega$ 2 Power Supply + C4 + 47μF C3 $\mathop{\gtrless}_{100\Omega}^{R2}$ 0.1μF V = 4V

Test Conditions: Frequency = 200Hz Duty Cycle = 0.2% V_{CC} = 15V to 30V V_{EE} = 0V

 $I_F = 7mA$ to 16mA

LED-IFmon

Figure 21. I_{OH} Test Circuit

 V_{OH}

5

Current Probe

To Scope

3

R1 100Ω

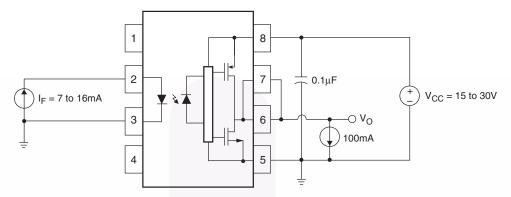


Figure 22. V_{OH} Test Circuit

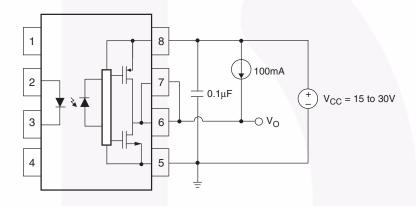


Figure 23. V_{OL} Test Circuit

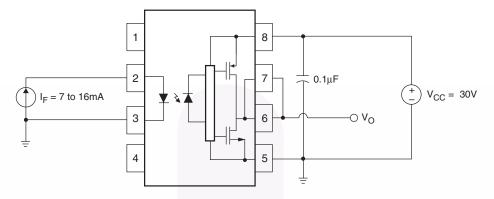


Figure 24. I_{CCH} Test Circuit

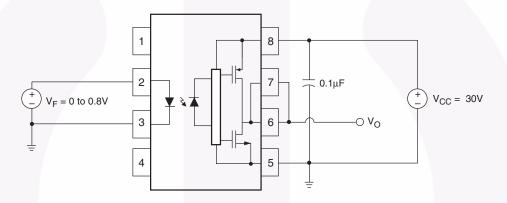


Figure 25. I_{CCL} Test Circuit

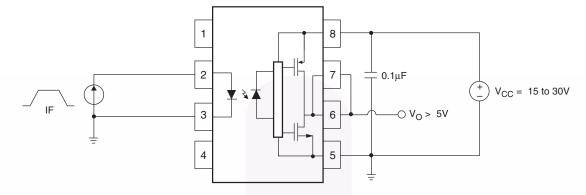


Figure 26. I_{FLH} Test Circuit

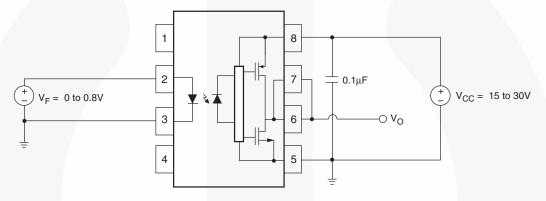


Figure 27. V_{FHL} Test Circuit

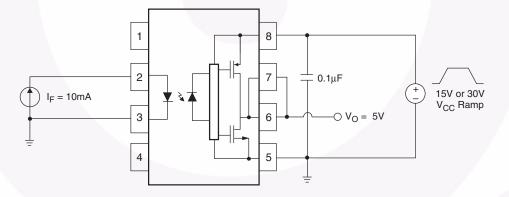
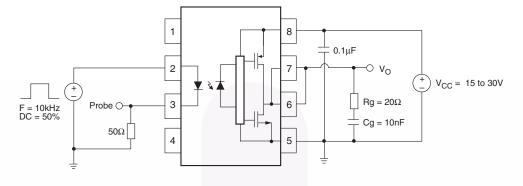


Figure 28. UVLO Test Circuit



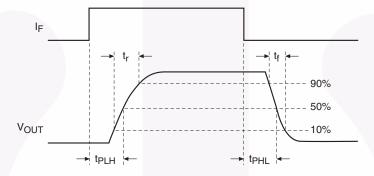
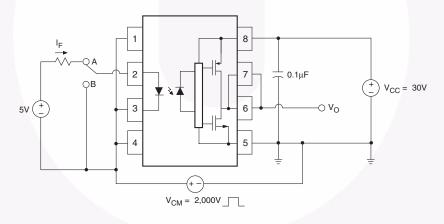


Figure 29. t_{PHL} , t_{PLH} , t_{R} and t_{F} Test Circuit and Waveforms



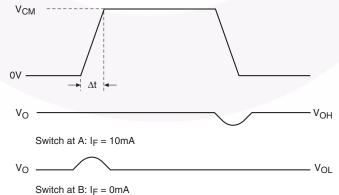
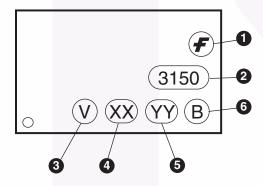


Figure 30. CMR Test Circuit and Waveforms

Ordering Information

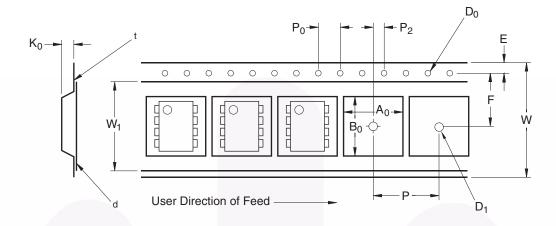
Part Number	Package	Packing Method
FOD3150	DIP 8-Pin	Tube (50 units per tube)
FOD3150S	SMT 8-Pin (Lead Bend)	Tube (50 units per tube)
FOD3150SD	SMT 8-Pin (Lead Bend)	Tape and Reel (1,000 units per reel)
FOD3150V	DIP 8-Pin, IEC60747-5-2 option	Tube (50 units per tube)
FOD3150SV	SMT 8-Pin (Lead Bend), IEC60747-5-2 option	Tube (50 units per tube)
FOD3150SDV	SMT 8-Pin (Lead Bend), IEC60747-5-2 option	Tape and Reel (1,000 units per reel)
FOD3150T	DIP 8-Pin, 0.4" Lead Spacing	Tube (50 units per tube)
FOD3150TV	DIP 8-Pin, 0.4" Lead Spacing , IEC60747-5-2 option	Tube (50 units per tube)

Marking Information



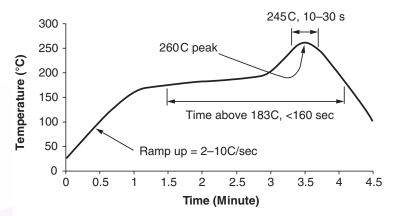
Definitions					
1	Fairchild logo				
2	Device number				
3	IEC60747-5-2 Option (only appears on component ordered with this option)				
4	Two digit year code, e.g., '08'				
5	Two digit work week ranging from '01' to '53'				
6	Assembly package code				

Carrier Tape Specifications

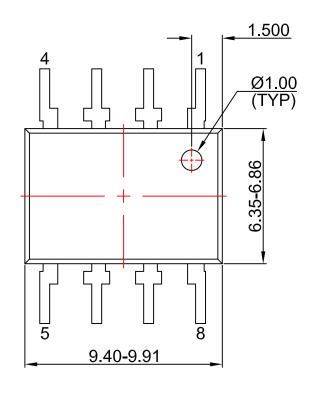


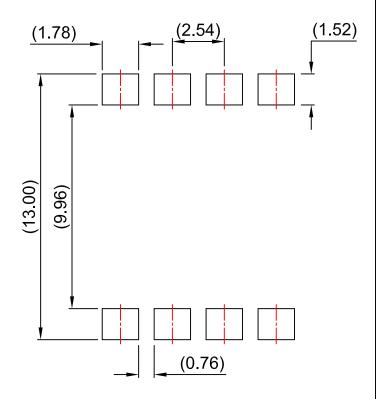
Symbol	Description	Dimension in mm
W	Tape Width	16.0 ± 0.3
t	Tape Thickness	0.30 ± 0.05
P ₀	Sprocket Hole Pitch	4.0 ± 0.1
D ₀	Sprocket Hole Diameter	1.55 ± 0.05
Е	Sprocket Hole Location	1.75 ± 0.10
F	Pocket Location	7.5 ± 0.1
P ₂		2.0 ± 0.1
Р	Pocket Pitch	12.0 ± 0.1
A ₀	Pocket Dimensions	10.30 ±0.20
B ₀		10.30 ±0.20
K ₀		4.90 ±0.20
W ₁	Cover Tape Width	13.2 ± 0.2
d	Cover Tape Thickness	0.1 max
	Max. Component Rotation or Tilt	10°
R	Min. Bending Radius	30

Reflow Profile

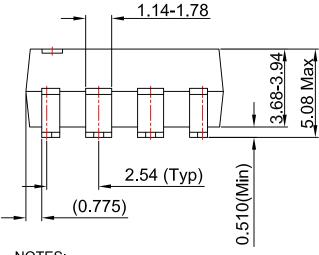


- Peak reflow temperature: 260 C (package surface temperature) Time of temperature higher than 183 C for 160 seconds or less One time soldering reflow is recommended



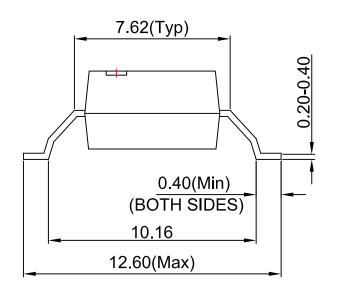






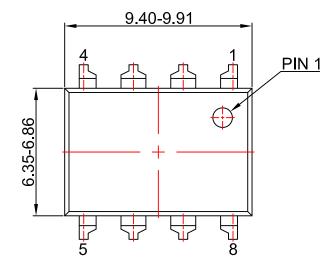


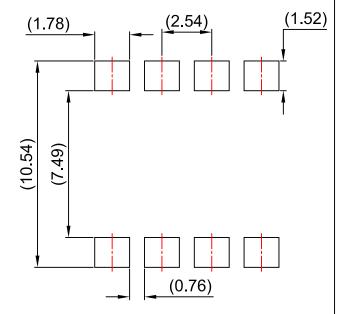
- A) NO STANDARD APPLIES TO THIS PACKAGE
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION
- D) DWG FILENAME AND REVISION: MKT-N08Lrev2.

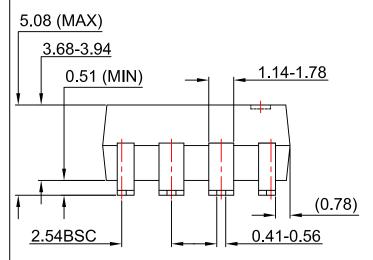




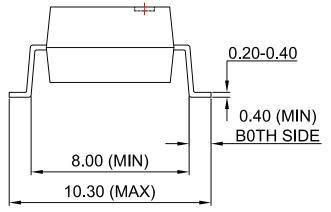








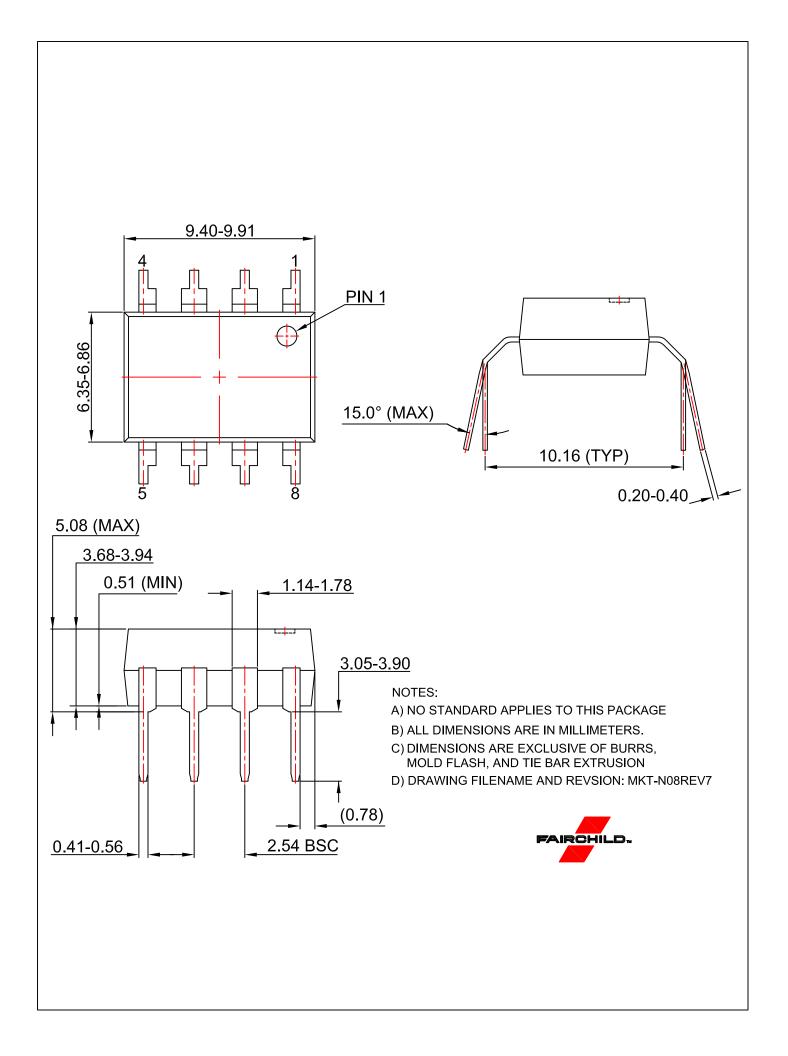




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